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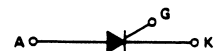
**2N1595
 thru
 2N1599**

Silicon Controlled Rectifiers Reverse Blocking Triode Thyristors

These devices are glassivated planar construction designed for gating operation in mA/ μ A signal or detection circuits.

- Low-Level Gate Characteristics — $I_{GT} = 10 \text{ mA (Max) @ } 25^\circ\text{C}$
- Low Holding Current — $I_H = 5 \text{ mA (Typ) @ } 25^\circ\text{C}$
- Glass-to-Metal Bond for Maximum Hermetic Seal

**SCRs
 1.6 AMPERES RMS
 50 thru 600 VOLTS**



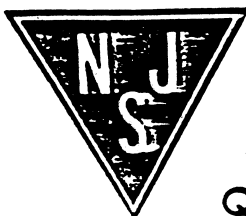
**CASE 79-02
 TO-39**

***MAXIMUM RATINGS** ($T_J = 125^\circ\text{C}$ unless otherwise noted, $R_{GC} = 1 \text{ k}\Omega$.)

Rating	Symbol	Value	Unit
Repetitive Peak Reverse Blocking Voltage (1)	VRRM	50	Volts
		100	
		200	
		300	
		400	
Repetitive Peak Forward Blocking Voltage (1)	VDRM	50	Volts
		100	
		200	
		300	
		400	
RMS On-State Current (All Conduction Angles)	$I_T(\text{RMS})$	1.6	Amps
Peak Non-Repetitive Surge Current (One Cycle, 60 Hz, $T_J = -65 \text{ to } +125^\circ\text{C}$)	I_{TSM}	15	Amps
Peak Gate Power	PGM	0.1	Watt
Average Gate Power	PG(AV)	0.01	Watt
Peak Gate Current	I_{GM}	0.1	Amp
Peak Gate Voltage — Forward Reverse	VGFM	10	Volts
	VGRM	10	
Operating Junction Temperature Range	T_J	-65 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$

*Indicates JEDEC Registered Data.

(1) VDRM or VRRM for all types can be applied on a continuous DC basis without incurring damage.



Quality Semi-Conductors